







CD74HCT03, CD54HCT03 SCHS414 - JUNE 2020

# CDx4HCT03 Quadruple 2-Input NAND Gates with Open-Drain Outputs

# 1 Features

- · LSTTL input logic compatible
- $\label{eq:linear} \begin{array}{l} \quad V_{IL(max)} = 0.8 \ \text{V}, \ V_{IH(min)} = 2 \ \text{V} \\ \text{CMOS input logic compatible} \end{array}$ 
  - I<sub>I</sub> ≤ 1 µA at V<sub>OL</sub>, V<sub>OH</sub>
- **Buffered** inputs
- 4.5 V to 5.5 V operation ٠
- Wide operating temperature range: • -55°C to +125°C
- Supports fanout up to 10 LSTTL loads
- ٠ Significant power reduction compared to LSTTL logic ICs

## 2 Applications

- Alarm / tamper detect circuit •
- S-R latch

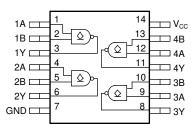
# **3 Description**

This device contains four independent 2-input NAND gates with open-drain outputs. Each gate performs the Boolean function  $Y = \overline{A \bullet B}$  in positive logic.

Device Information <sup>(1)</sup>									
PART NUMBER	PACKAGE	BODY SIZE (NOM)							
	SOIC (14)	9 70 mm x 2 00 mm							

	TAGRAGE	BODT OILE (ITOIII)
CD74HCT03M	SOIC (14)	8.70 mm × 3.90 mm
CD74HCT03E	PDIP (14)	19.30 mm × 6.40 mm
CD54HCT03F	CDIP (14)	21.30 mm × 7.60 mm

(1)For all available packages, see the orderable addendum at the end of the data sheet.



**Functional pinout** 





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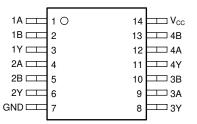
# 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
June 2020	*	Initial release.



# **5** Pin Configuration and Functions



# Figure 5-1. D, N, or J Package 14-Pin SOIC, PDIP, or CDIP Top View

### **Pin Functions**

PIN		- I/O	DESCRIPTION							
NAME	NO.		DESCRIPTION							
1A	1	Input	Channel 1, Input A							
1B	2	Input	Channel 1, Input B							
1Y	3	Output	Channel 1, Output Y							
2A	4	Input	Channel 2, Input A							
2B	5	Input	Channel 2, Input B							
2Y	6	Output	Channel 2, Output Y							
GND	7	_	Ground							
3Y	8	Output	Channel 3, Output Y							
3A	9	Input	Channel 3, Input A							
3B	10	Input	Channel 3, Input B							
4Y	11	Output	Channel 4, Output Y							
4A	12	Input	Channel 4, Input A							
4B	13	Input	Channel 4, Input B							
V <sub>CC</sub>	14	_	Positive Supply							



# 6 Specifications

## 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		-0.5	7	V
I <sub>IK</sub>	Input clamp current <sup>(2)</sup>	$V_{I} < -0.5 V \text{ or } V_{I} > V_{CC} + 0.5 V$		±20	mA
I <sub>OK</sub>	Output clamp current <sup>(2)</sup>	$V_{O}$ < -0.5 V or $V_{O}$ > $V_{CC}$ + 0.5 V		±20	mA
Ι <sub>ΟΚ</sub>	Continuous output current		±25	mA	
	Open drain output current	V <sub>O</sub> > -0.5 V		-25	mA
	Continuous current through $V_{CC}$ or GND			±50	mA
-	lun tim to me antum (3)	Plastic package		150	°C
lj	Junction temperature <sup>(3)</sup>	Hermetic package or die		175	°C
	Maximum lead temperature (soldering 10s)	SOIC - lead tips only		300	°C
T <sub>stg</sub>	Storage temperature	1	65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

(3) Guaranteed by design.

### 6.2 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage		4.5		5.5	V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2			V
VIL	Low-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V			0.8	V
VI	Input voltage		0		V <sub>CC</sub>	V
Vo	Output voltage		0		V <sub>CC</sub>	V
+	Input transition time	V <sub>CC</sub> = 4.5 V			500	20
tt	Input transition time	V <sub>CC</sub> = 5.5 V			400	ns
T <sub>A</sub>	Operating free-air temperature		-55		125	°C

### 6.3 Thermal Information

		CD74	CD74HCT03					
	THERMAL METRIC <sup>(1)</sup>	N (PDIP)	D (SOIC)	UNIT				
		14 PINS	14 PINS					
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	65.4	102.7	°C/W				
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	53.1	59.2	°C/W				
R <sub>θJB</sub>	Junction-to-board thermal resistance	45.1	58.6	°C/W				
$\Psi_{JT}$	Junction-to-top characterization parameter	32.7	20.3	°C/W				
$\Psi_{JB}$	Junction-to-board characterization parameter	44.9	58.2	°C/W				
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W				

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



### **6.4 Electrical Characteristics**

							Opera	ting free	-air tem	peratur	e (T <sub>A</sub> )					
F	PARAMETER	AMETER TEST CONDITIONS		TEST CONDITIONS		V <sub>cc</sub>		25°C		<b>-40</b> °	°C to 85	°C	–55°	C to 125	5°C	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX			
V <sub>OL</sub>	Low-level output		Ι <sub>ΟL</sub> = 20 μΑ	4.5 V			0.1			0.1			0.1	V		
	voltage V	VIL	I <sub>OL</sub> = 4 mA	4.5 V			0.26			0.33			0.4			
I	Input leakage current	V <sub>I</sub> = V <sub>CC</sub> and GND	I <sub>O</sub> = 0	5.5 V			±0.1			±1			±1	μA		
I <sub>CC</sub>	Supply current	V <sub>I</sub> = V <sub>CC</sub> or GND	I <sub>O</sub> = 0	5.5 V			2			20			40	μA		
ΔI <sub>CC</sub>	Additional Quiescent Device Current Per Input Pin	V <sub>I</sub> = V <sub>CC</sub> – 2.1		4.5 V to 5.5 V		100	360			450			490	μΑ		
Ci	Input capacitance			5 V			10			10			10	pF		

over operating free-air temperature range; typical values measured at T<sub>A</sub> = 25°C (unless otherwise noted).

(1) For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4 V, V<sub>CC</sub> = 5.5 V) specification is 1.8 mA.

#### 6.5 Switching Characteristics

over operating free-air temperature range; typical values measured at TA = 25°C (unless otherwise noted).

	TES			TEST		Operating free-air temperature					ure (T <sub>/</sub>	re (T <sub>A</sub> )			
	PARAMETER				Vcc	V <sub>CC</sub> 25°	25°C	C –40°C to 85		5°C	–55°C to 125°C			UNIT	
				NS		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
+	Propagation dolay	A or B	Y	C <sub>L</sub> = 50 pF	4.5 V			24			30			36	ns
<sup>1</sup> pd	t <sub>pd</sub> Propagation delay	A or B	Y	C <sub>L</sub> = 15 pF	5 V		9								115
t	Transition-time		Y	C <sub>L</sub> = 50 pF	4.5 V			15			19			22	ns

### 6.6 Operating Characteristics

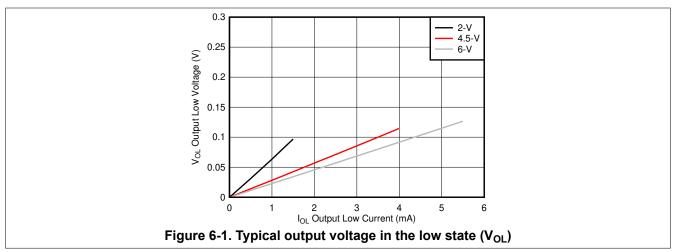
over operating free-air temperature range; typical values measured at T<sub>A</sub> = 25°C (unless otherwise noted).

	PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	MIN	TYP MAX	UNIT
C <sub>pd</sub>	Power dissipation capacitance per gate	No load	5 V		9	pF

### 6.7 Typical Characteristics

T<sub>A</sub> = 25°C

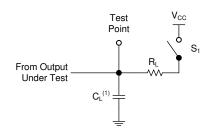


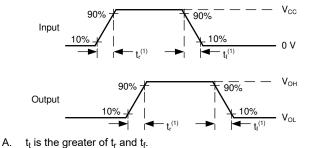




### 7 Parameter Measurement Information

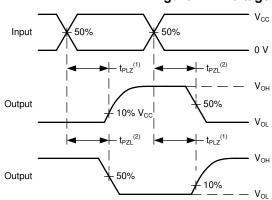
- Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z<sub>O</sub> = 50 Ω, t<sub>t</sub> < 6 ns.</li>
- The outputs are measured one at a time, with one input transition per measurement.





A. C<sub>L</sub>= 50 pF and includes probe and jig capacitance. **Figure 7-1. Load Circuit** 

Figure 7-2. Voltage Waveforms Transition Times



A. The maximum between  $t_{PLH}$  and  $t_{PHL}$  is used for  $t_{pd}$ .

#### Figure 7-3. Voltage Waveforms Propagation Delays

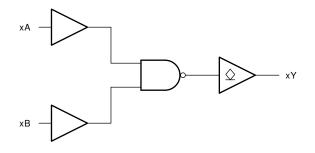


# 8 Detailed Description

### 8.1 Overview

This device contains four independent 2-input NAND gates with open-drain outputs. Each gate performs the Boolean function  $Y = \overline{A \bullet B}$  in positive logic.

#### 8.2 Functional Block Diagram



#### 8.3 Feature Description

#### 8.3.1 CMOS Open-Drain Outputs

The open-drain output allows the device to sink current to GND but not to source current from  $V_{CC}$ . When the output is not actively pulling the line low, it will go into a high impedance state. This allows the device to be used for a wide variety of applications, including up-translation and down-translation, as the output voltage can be determined by an external pull-up resistor.

The current drive capability of this device creates fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the power output of the device to be limited to avoid thermal runaway and damage due to over-current. The electrical and thermal limits defined the in the *Section 6.1* must be followed at all times.

The CD74HCT03 can drive a load with a total capacitance less than or equal to the maximum load listed in the *Section 6.5* connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed the provided load value. If larger capacitive loads are required, it is recommended to add a series resistor between the output and the capacitor to limit output current to the values given in the *Section 6.1*.

#### 8.3.2 TTL-Compatible CMOS Inputs

TTL-Compatible CMOS inputs are high impedance and are typically modeled as a resistor from the input to ground in parallel with the input capacitance given in the *Section 6.4*. The worst case resistance is calculated with the maximum input voltage, given in the *Section 6.1*, and the maximum input leakage current, given in the *Section 6.4*, using ohm's law ( $R = V \div I$ ).

Signals applied to the inputs need to have fast edge rates, as defined by  $\Delta t/\Delta v$  in the Section 6.2 to avoid excessive current consumption and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be used to condition the input signal prior to the TTL-compatible CMOS input.

TTL-Compatible CMOS inputs have a lower threshold voltage than standard CMOS inputs to allow for compatibility with older bipolar logic devices. See the *Section* 6.2 for the valid input voltages for the CD74HCT03.

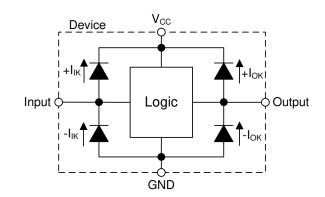


### 8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in Figure 8-1.

#### CAUTION

Voltages beyond the values specified in the Section 6.1 table can cause damage to the device. The recommended input and output voltage ratings may be exceeded if the input and output clampcurrent ratings are observed.



#### Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

#### 8.4 Device Functional Modes

INP	UTS	OUTPUT							
A	В	Y							
Н	Н	L							
L	Х	Z							
Х	L	Z							

#### Table 8-1. Function Table



### **9** Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

#### 9.1 Application Information

In this application, one 2-input open-drain NAND gate is used as shown in *Figure 9-1*. The other three gates can be used for other applications in the system, or the inputs can be grounded and the channels left unused.

This device is used to directly control an LED. The LED is on when the inputs are both high, and off any other time.

#### 9.2 Typical Application

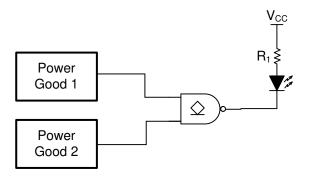


Figure 9-1. Typical application schematic

#### 9.2.1 Design Requirements

#### 9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the Section 6.2. The supply voltage sets the device's electrical characteristics as described in the Section 6.4.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the CD74HCT03 plus the maximum supply current,  $I_{CC}$ , listed in *Section 6.4*. The logic device can only sink as much current as is provided by the external pull-up resistor or other supply source. Be sure not to exceed the maximum total current through GND listed in the *Section 6.1*.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and  $C_{pd}$  Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

#### CAUTION

The maximum junction temperature,  $T_J(max)$  listed in the Section 6.1, is an additional limitation to prevent damage to the device. Do not violate any values listed in the Section 6.1. These limits are provided to prevent damage to the device.

#### 9.2.1.2 Input Considerations

Unused inputs must be terminated to either  $V_{CC}$  or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used



for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the CD74HCT03, as specified in the Section 6.4, and the desired input transition rate. A  $10-k\Omega$  resistor value is often used due to these factors.

Refer to the Section 8.3 for additional information regarding the inputs for this device.

#### 9.2.1.3 Output Considerations

The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the *Section 6.4*. The plot in provides a typical relationship between output voltage and current for this device.

Open-drain outputs can be directly connected together to produce a wired-AND. This is possible because the outputs cannot source current, and thus can never be in bus-contention.

Unused outputs can be left floating. Do not connect outputs directly to V<sub>CC</sub> or ground.

Refer to Section 8.3 for additional information regarding the outputs for this device.

#### 9.2.2 Detailed Design Procedure

- 1. Add a decoupling capacitor from V<sub>CC</sub> to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V<sub>CC</sub> and GND pins. An example layout is shown in the Section 11.
- Ensure the capacitive load at the output is ≤ 70 pF. This is not a hard limit, however it will ensure optimal
  performance. This can be accomplished by providing short, appropriately sized traces from the CD74HCT03
  to the receiving device.
- Ensure the resistive load at the output is larger than (V<sub>CC</sub> / I<sub>O</sub>(max)) Ω. This will ensure that the maximum output current from the Section 6.1 is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
- 4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation

#### 9.2.3 Application Curves

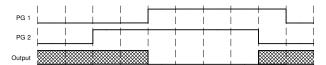


Figure 9-2. Typical application timing diagram



## **10 Power Supply Recommendations**

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Section 6.2*. Each V<sub>CC</sub> terminal should have a bypass capacitor to prevent power disturbance. A 0.1- $\mu$ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in *Figure 11-1*.



## 11 Layout

### **11.1 Layout Guidelines**

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.

#### **11.2 Layout Example**

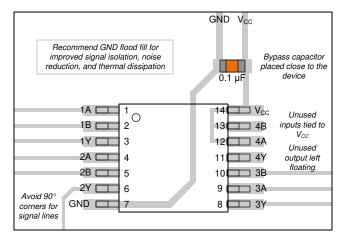


Figure 11-1. Example layout for the CD74HCT03



# 12 Device and Documentation Support

### **12.1 Documentation Support**

#### 12.1.1 Related Documentation

For related documentation see the following:

- HCMOS Design Considerations
- CMOS Power Consumption and CPD Calculation
- Designing with Logic

### 12.2 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

### 12.3 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

#### 12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 12.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

### 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



### PACKAGING INFORMATION

Orderable Device	Status	Package Type		Pins	-	Eco Plan	Lead finish/	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	Ball material	(3)		(4/5)	
							(6)		-		
CD54HCT03F3A	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HCT03F3A	Samples
CD74HCT03E	ACTIVE	PDIP	Ν	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT03E	Samples
CD74HCT03M	OBSOLETE	SOIC	D	14		TBD	Call TI	Call TI	-55 to 125	НСТ03М	
CD74HCT03M96	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-55 to 125	НСТОЗМ	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF CD54HCT03, CD74HCT03 :

• Catalog : CD74HCT03

Military : CD54HCT03

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications



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### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



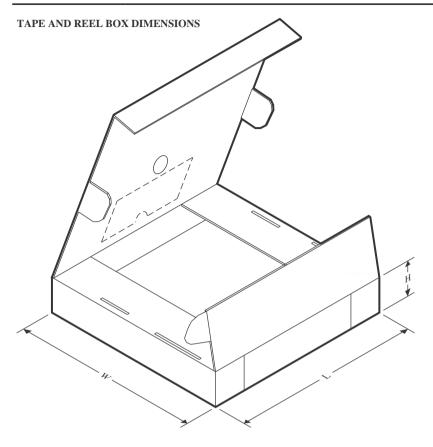
*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HCT03M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD74HCT03M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD74HCT03M96	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1



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# PACKAGE MATERIALS INFORMATION

12-May-2023



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HCT03M96	SOIC	D	14	2500	356.0	356.0	35.0
CD74HCT03M96	SOIC	D	14	2500	356.0	356.0	35.0
CD74HCT03M96	SOIC	D	14	2500	366.0	364.0	50.0

# TEXAS INSTRUMENTS

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## TUBE



# - B - Alignment groove width

\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
CD74HCT03E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HCT03E	N	PDIP	14	25	506	13.97	11230	4.32

# **D0014A**



# **PACKAGE OUTLINE**

# SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



# D0014A

# **EXAMPLE BOARD LAYOUT**

# SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# D0014A

# **EXAMPLE STENCIL DESIGN**

# SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



# **GENERIC PACKAGE VIEW**

# CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



# J0014A



# **PACKAGE OUTLINE**

# CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



NOTES:

- 1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This package is hermitically sealed with a ceramic lid using glass frit.
- Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
   Falls within MIL-STD-1835 and GDIP1-T14.



# J0014A

# **EXAMPLE BOARD LAYOUT**

# CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE





# N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- $\triangle$  The 20 pin end lead shoulder width is a vendor option, either half or full width.



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